



# N-Channel 30-V (D-S) MOSFET

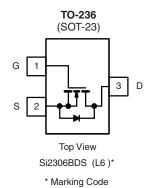
PRODUCT SUMMARY					
V <sub>DS</sub> (V)	$R_{DS(on)}(\Omega)$	I <sub>D</sub> (A)	Q <sub>g</sub> (Typ.)		
30	0.047 at V <sub>GS</sub> = 10 V	4.0	3.0		
	0.065 at V <sub>GS</sub> = 4.5 V	3.5	3.0		

#### **FEATURES**

- Halogen-free Option Available
- TrenchFET® Power MOSFET
- 100 % R<sub>g</sub> Tested







Ordering Information: Si2306BDS-T1-E3 (Lead (Pb)-free)

Si2306BDS-T1-GE3 (Lead (Pb)-free and Halogen-free)

ABSOLUTE MAXIMUM RATINGS T <sub>A</sub> = 25 °C, unless otherwise noted						
Parameter		Symbol	5 s	Steady State	Unit	
Drain-Source Voltage		V <sub>DS</sub>	30		V	
Gate-Source Voltage		V <sub>GS</sub>	± 20			
Continuous Brain Comment /T 150 °C\2 b	T <sub>A</sub> = 25 °C	I <sub>D</sub>	4.0	3.16		
Continuous Drain Current (T <sub>J</sub> = 150 °C) <sup>a, b</sup>	T <sub>A</sub> = 70 °C		3.5	2.7		
Pulsed Drain Current		I <sub>DM</sub>	20		Α	
Continuous Source Current (Diode Conduction) <sup>a, b</sup>	I <sub>S</sub>	1.04	0.62			
	T <sub>A</sub> = 25 °C	P <sub>D</sub>	1.25	0.75	w	
Maximum Power Dissipation <sup>a, b</sup>	T <sub>A</sub> = 70 °C		0.8	0.48		
Operating Junction and Storage Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	- 55 t	o 150	°C		

THERMAL RESISTANCE RATINGS						
Parameter		Symbol	Typical	Maximum	Unit	
Manifestor Localitan to Applicant	t ≤ 5 s	- R <sub>thJA</sub>	80	100	°C/W	
Maximum Junction-to-Ambient <sup>a</sup>	Steady State		130	166		
Maximum Junction-to-Foot (Drain)	Steady State	$R_{thJF}$	60	75		

#### Notes:

- a. Surface Mounted on FR4 board,  $t \le 5 \text{ s.}$
- b. Pulse width limited by maximum junction temperature.
- c. Surface Mounted on FR4 board.

For SPICE model information via the Worldwide Web: http://www.vishay.com/www/product/spice.htm

# Vishay Siliconix

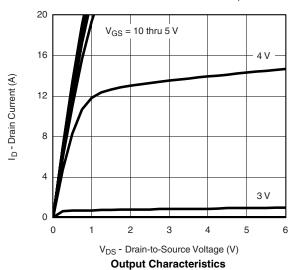


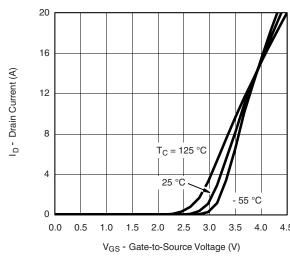
			Limits				
Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit	
Static							
Drain-Source Breakdown Voltage	V <sub>(BR)DSS</sub>	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$	30			V	
Gate-Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}, I_D = 250 \mu A$	1.0		3.0	<b>V</b>	
Gate-Body Leakage	I <sub>GSS</sub>	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			± 100	nA	
Zero Gate Voltage Drain Current	l	V <sub>DS</sub> = 30 V, V <sub>GS</sub> = 0 V			0.5	μΑ	
Zero Gate voltage Drain Current	IDSS	$V_{DS} = 30 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55 ^{\circ}\text{C}$			10		
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	$V_{DS} \ge 4.5 \text{ V}, V_{GS} = 10 \text{ V}$	6			Α	
Durin Course On Braintana		$V_{GS} = 10 \text{ V}, I_D = 3.5 \text{ A}$		0.038	0.047	Ω	
Drain-Source On-Resistance <sup>a</sup>	R <sub>DS(on)</sub>	$V_{GS} = 4.5 \text{ V}, I_D = 2.8 \text{ A}$ 0.052		0.065	_ 12		
Forward Transconductance <sup>a</sup>	g <sub>fs</sub>	$V_{DS} = 4.5 \text{ V}, I_{D} = 2.5 \text{ A}$		7.0		S	
Diode Forward Voltage	$V_{SD}$	I <sub>S</sub> = 1.25 A, V <sub>GS</sub> = 0 V		0.8	1.2	V	
Dynamic							
Gate Charge	Qg	$V_{DS} = 15 \text{ V}, V_{GS} = 5 \text{ V}, I_{D} = 2.5 \text{ A}$		3.0	4.5		
Total Gate Charge	Q <sub>gt</sub>			6	9	nC	
Gate-Source Charge	$Q_{gs}$	$V_{DS} = 15 \text{ V}, V_{GS} = 10 \text{ V}, I_{D} = 2.5 \text{ A}$		1.6		110	
Gate-Drain Charge	$Q_{gd}$			0.6			
Gate Resistance	$R_{g}$	f = 1.0 MHz	2.5	5	7.5	Ω	
Input Capacitance	C <sub>iss</sub>			305			
Output Capacitance	C <sub>oss</sub>	$V_{DS} = 15 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$		65		pF	
Reverse Transfer Capacitance	C <sub>rss</sub>			29			
Switching							
Turn-On Delay Time	t <sub>d(on)</sub>			7	11		
Rise Time	t <sub>r</sub>	$V_{DD}$ = 15 V, $R_L$ = 15 $\Omega$		12	18	ns	
Turn-Off Delay Time	t <sub>d(off)</sub>	$I_D\cong$ 1 A, $V_{GEN}$ = 10 V, $R_g$ = 6 $\Omega$		14	25		
Fall Time	ì,			6	10		
Reverse Recovery Time	t <sub>rr</sub>	I <sub>F</sub> = 1.25 A, di/dt = 100 A/μs		14	21		
Body Diode Reverse Recovery Charge	Q <sub>rr</sub>	$I_F = 1.25 \text{ A}, \text{ u/u} = 100 \text{ A/}\mu\text{S}$		6	10	nC	

#### Notes:

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

## TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted





**Transfer Characteristics** 

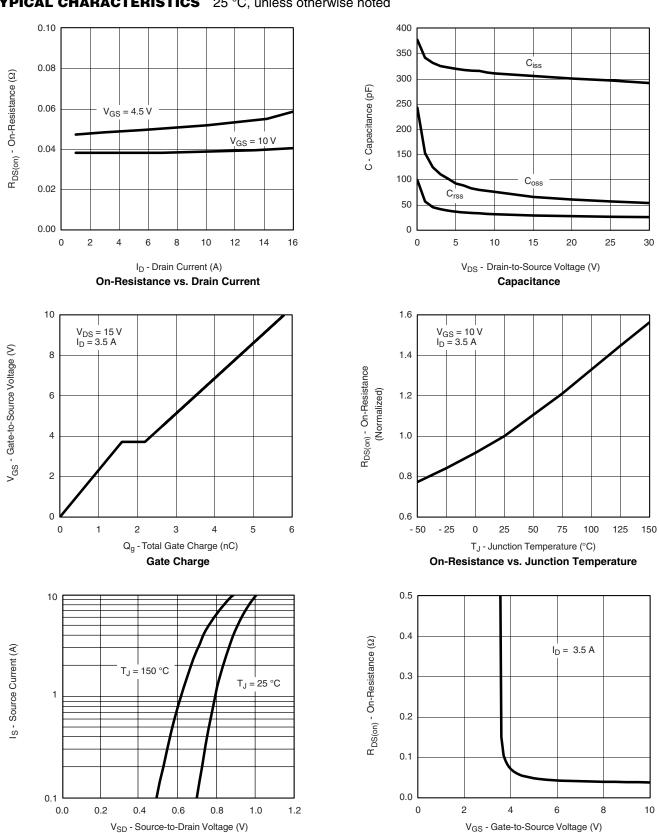
a. Pulse test: Pulse width  $\leq$  300  $\mu$ s, duty cycle  $\leq$  2 %.







### TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



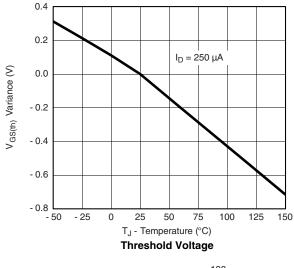
Source-Drain Diode Forward Voltage

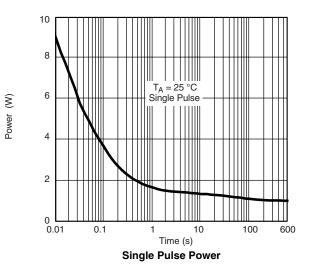
On-Resistance vs. Gate-to-Source Voltage

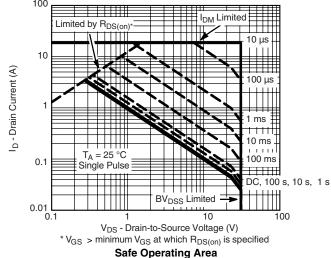
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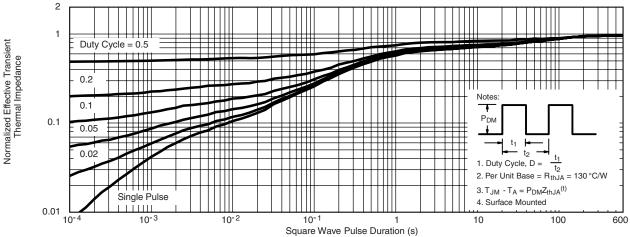
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## TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted









Normalized Thermal Transient Impedance, Junction-to-Ambient

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see <a href="http://www.vishay.com/ppg?73234">http://www.vishay.com/ppg?73234</a>.

Vishay Siliconix

# SOT-23 (TO-236): 3-LEAD







Dim	MILLI	METERS	INCHES			
	Min	Max	Min	Max		
Α	0.89	1.12	0.035	0.044		
A <sub>1</sub>	0.01	0.10	0.0004	0.004		
A <sub>2</sub>	0.88	1.02	0.0346	0.040		
b	0.35	0.50	0.014	0.020		
С	0.085	0.18	0.003	0.007		
D	2.80	3.04	0.110	0.120		
E	2.10	2.64	0.083	0.104		
E <sub>1</sub>	1.20	1.40	0.047	0.055		
е	0.95 BSC		0.037	0.0374 Ref		
e <sub>1</sub>	1.90 BSC		0.074	0748 Ref		
L	0.40	0.60	0.016	0.024		
L <sub>1</sub>	0.64 Ref		0.025	5 Ref		
S	0.50 Ref		0.020	) Ref		
q	3°	8°	3°	8°		
FCN: S-03946-Rev K 09-	lul-01	•				

ECN: S-03946-Rev. K, 09-Jul-01

DWG: 5479

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#### **RECOMMENDED MINIMUM PADS FOR SOT-23**



Recommended Minimum Pads Dimensions in Inches/(mm)

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APPLICATION NOTE



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